AMENDMENTS TO THE CLAIMS

Please rewrite the claims as follows:

1. (Currently Amended) A charged-particle-beam exposure apparatus for exposing a substrate using a charged-particle-beam, comprising:

a charged-particle source ~~for emitting~~ configured to emit a charged-particle beam;

a plate configured to selectively passing the charged-particle beam for exposing the substrate;

a detecting unit configured to detect intensity of that part of the charged-particle beam, which has been emitted from said charged-particle source, said detecting unit detects the intensity of the charged-particle beam at a plurality of locations on the plate in an area not utilized in exposing the substrate; and

an adjusting unit configured to adjust intensity distribution of the charged-particle beam based upon result of detection by said detecting unit.

2. (Original) The apparatus according to claim 1, wherein said adjusting unit adjusts optical power of electrostatic lenses that construct a collimator lens for substantially collimating the charged-particle beam that has been emitted from said charged-particle source.

3. (Original) The apparatus according to claim 1, further comprising a storage unit configured to store, as a reference value, the intensity detected by said detecting unit in a state in which the intensity distribution of the charged-particle beam can be regarded as uniform;

wherein said unit adjusts the intensity distribution of the charged particles based upon a difference between the intensity detected by said detecting unit and the reference value.

4. (Original) The apparatus according to claim 3, wherein said adjusting unit adjusts the intensity distribution of the charged-particle beam in such a manner that the intensity detected by said detecting unit will become the reference value.

5. (Original) The apparatus according to claim 3, further comprising:

a measuring unit configured to measure the intensity distribution of the charged-particle beam on the substrate to be exposed; and

a setting unit configured to set the intensity of the charged-particle beam, which has been detected by said detecting unit, to the reference value after the intensity distribution of the charged-particle beam has been adjusted to uniformity based upon the intensity distribution measured by said measuring unit.

6. (Original) The apparatus according to claim 3, wherein said adjusting unit halts processing for exposing the substrate and executes adjustment of the intensity distribution of the charged-particle beam if the difference between the intensity detected by said detecting unit and the reference value exceeds an allowable value.

7. (Previously Presented) The apparatus according to claim 1, wherein said plate has a plurality of apertures for dividing the charged-particle beam from said charged-particle source into a plurality of charged-particle beams used in exposing the substrate and

wherein the plurality of locations are in a portion where the plurality of apertures are non-existent.

8. (Previously Presented) The apparatus according to claim 1, wherein said plate comprises a stencil mask for allowing the charged-particle beam from said charged-particle source to pass through in accordance with a pattern and expose the substrate and

wherein the plurality of locations are in an area of the stencil mask other than an area in which the pattern is present.

9. (Previously Presented) A method of controlling a charged-particle-beam exposure apparatus for exposing a substrate using a charged-particle beam, comprising:

a detecting step of detecting, by a detector provided for the purpose of detecting intensity of a charged-particle beam, intensity of that part of the charged-particle beam, which has been emitted from a charged-particle source, said detecting step detects the intensity of the charged-particle beam at a plurality of locations on a plate, configured to selectively pass the charged-particle beam for exposing the substrate, in an area not utilized in exposing the substrate; and

an adjusting step of adjusting intensity distribution of the charged-particle beam based upon result of detection at said detecting step.

10. (Original) The method according to claim 9, wherein said adjusting step adjusts optical power of electrostatic lenses that construct a collimator lens for substantially collimating the charged-particle beam that has been emitted from the charged-particle source

11. (Original) The method according to claim 9, further comprising a storage step of storing, as a reference value, the intensity detected by said detector in a state in which the intensity distribution of the charged-particle beam can be regarded as uniform;

wherein said adjusting step adjusts the intensity distribution of the charged particles based upon a difference between the intensity detected at said detecting step and the reference value.

12. (Original) The method according to claim 11, wherein said adjusting step adjusts the intensity distribution of the charged-particle beam in such a manner that the intensity detected at said detecting step will become the reference value.

13. (Original) The method according to claim 11, further comprising:

a measuring step of measuring the intensity distribution of the charged-particle beam on the substrate to be exposed; and

a setting step of setting the intensity of the charged-particle beam, which has been detected by said detector, to the reference value after the intensity distribution of the charged-particle beam has been adjusted to uniformity based upon the intensity distribution measured at said measuring step.

14. (Original) The method according to claim 11, wherein said adjusting step halts processing for exposing the substrate and executes adjustment of the intensity distribution of the charged-particle beam if the difference between the intensity detected at said detecting step and the reference value exceeds an allowable value.

15. (Previously Presented) The method according to claim 9, wherein the plate has a plurality of apertures for dividing the charged-particle beam from said charged-particle source into a plurality of charged-particle beams used in exposing the substrate and

wherein the plurality of locations are in a portion where the plurality of apertures are non-existent.

16. (Previously Presented) The method according to claim 9, wherein the plate has a stencil mask for allowing the charged-particle beam from said charged-particle source to pass through in accordance with a pattern and expose the substrate and

wherein the plurality of locations are in an area of the stencil mask other than an area in which the pattern is present.